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## ABSTRACT OF THE DISCLOSURE

A method of manufacturing thin film transistors on a substrate having an insulative surface comprises the steps of: (a) forming a plurality of island-shaped semiconductor layers on a substrate having an insulative surface; (b) implanting 5 dopant into first regions at outsides of a region designated for a channel region in each of the semiconductor layers directly or through a thin insulation film whose thickness is equal to or less than 50 nm by ion implantation to form lightly doped regions; and (c) implanting dopant into regions at outsides of the first regions in each of the semiconductor layers directly or through the thin insulation film to form 10 heavily doped source/drain regions whose impurity concentration is higher than that of the lightly doped regions.

20 25 30 35 40 45 50 55 60 65 70 75 80 85 90 95 100